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# **HSU276**

Silicon Schottky Barrier Diode for Mixer

## **HITACHI**

ADE-208-078F(Z)  
Rev 6  
June 1996

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### **Features**

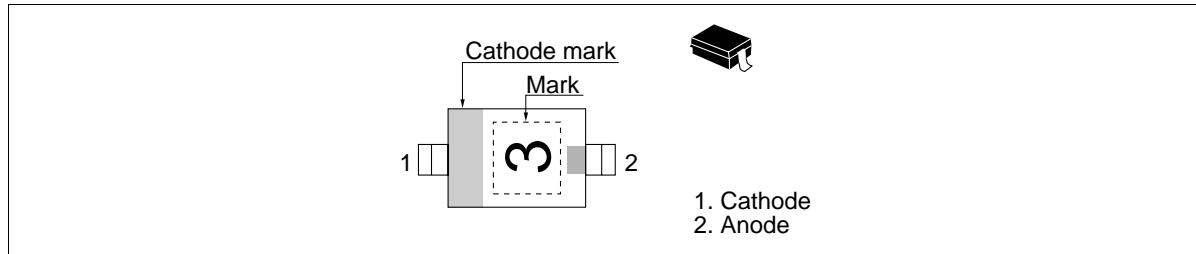
- High forward current, Low capacitance.
- Ultra small Resin Package (URP) is suitable for high density surface mounting and high speed assembly.

### **Ordering Information**

Type No.	Laser Mark	Package Code
HSU276	3	URP

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### **Outline**



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## HSU276

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### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Reverse voltage	VR	3	V
Average rectified current	IO	30	mA
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55~+125	°C

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### Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	VR	3	~	~	V	IR = 1 mA
Reverse current	IR	~	~	50	μA	VR = 0.5V
Forward current	IF	35	~	~	mA	VF = 0.5V
Capacitance	C	~	~	0.85	pF	VR = 0.5V, f = 1 MHz
ESD-Capability*1	~	30	~	~	V	C=200pF , Both forward and reverse direction 1 pulse.

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Notes 1. Failure criterion ; IR ≥ 100μA at VR =0.5 V

## Main Characteristic

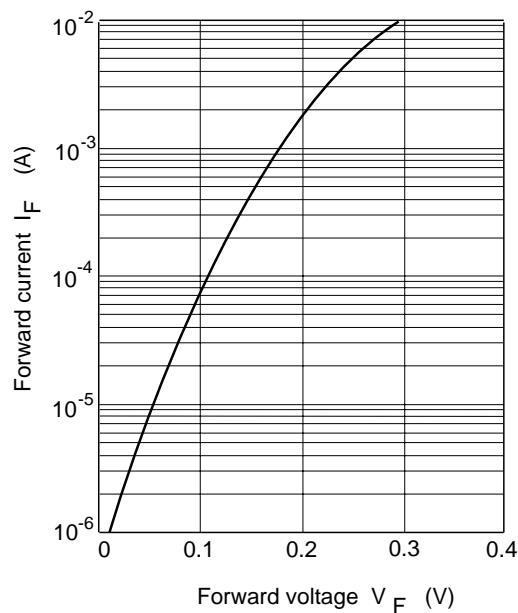


Fig.1 Forward current Vs. Forward voltage

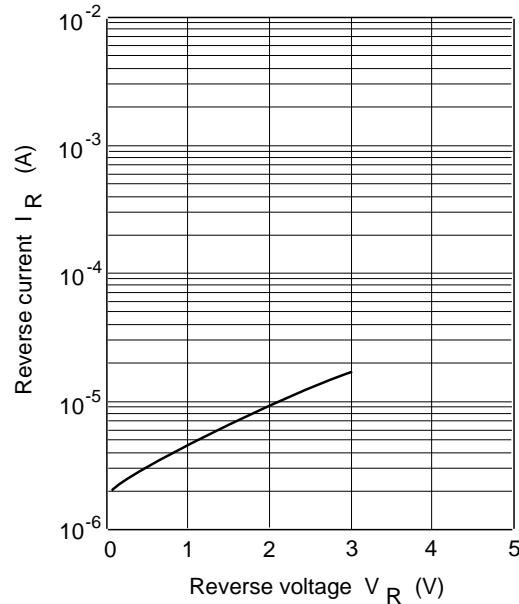


Fig.2 Reverse current Vs. Reverse voltage

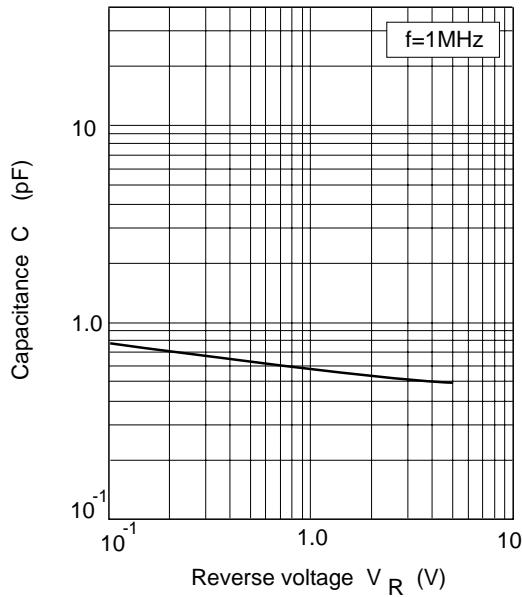


Fig.3 Capacitance Vs. Reverse voltage

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## HSU276

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### Package Dimensions

Unit : mm

